

## 600V, 30A, Trench FS II Fast IGBT

### General Description:

Using NCE's proprietary trench design and advanced FS (Field Stop) second generation technology, the 600V Trench FSIIIGBT offers superior conduction and switching performances, and easy parallel operation;

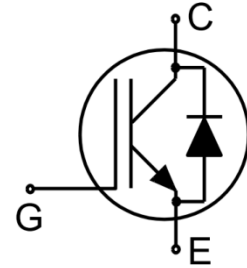
### Features

Trench FSII Technology offering

- Very low  $V_{CE(sat)}$
- High speed switching
- Positive temperature coefficient in  $V_{CE(sat)}$
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

### Application

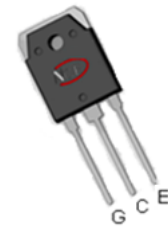
- Air Condition
- Inverters
- Motor drives



Schematic diagram

### Package Marking and Ordering Information

Device	Device Package	Device Marking
NCE30TH60BP	TO-3PNT	NCE30TH60BP



TO-3PNT

### Absolute Maximum Ratings ( $T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CES}$	Collector-Emitter Voltage	600	V
$V_{GES}$	Gate- Emitter Voltage	$\pm 30$	V
$I_C$	Collector Current	60	A
	Collector Current @ $T_C = 100^{\circ}\text{C}$	30	A
$I_{Cplus}$	Pulsed Collector Current, $t_p$ limited by $T_{jmax}$	90	A
-	turn off safe operating area, $V_{CE}=600\text{V}$ , $T_j=150^{\circ}\text{C}$	90	A
$I_F$	Diode Continuous Forward Current @ $T_C = 100^{\circ}\text{C}$	15	A
$I_{FM}$	Diode Maximum Forward Current	45	A
$P_D$	Power Dissipation @ $T_C = 25^{\circ}\text{C}$	183	W
	Power Dissipation @ $T_C = 100^{\circ}\text{C}$	73	W
$T_J, T_{stg}$	Operating Junction and Storage Temperature Range	-55 to +150	$^{\circ}\text{C}$
$T_L$	Maximum Temperature for Soldering	260	$^{\circ}\text{C}$
$t_{sc}$	Short circuit withstand time $V_{GE}=15.0\text{V}$ , $V_{CC}\leq 400\text{V}$ , Allowed number of short circuits<1000Time between short circuits: $\geq 1.0\text{s}, T_j\leq 150^{\circ}\text{C}$	3	us

**Thermal Characteristic**

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction to case for IGBT	0.68	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to case for Diode	1.08	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	40	°C/W

**Electrical Characteristics ( $T_c=25^\circ\text{C}$  unless otherwise noted)**

Symbol	Parameter	Test Conditions	Value			Units	
			Min.	Typ.	Max.		
<b>STATIC Characteristics</b>							
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$V_{GE}=0V, I_{CE}=1mA$	600	--	--	V	
$I_{CES}$	Collector-Emitter Leakage Current	$V_{GE}=0V, V_{CE}=600V$	--	--	4	uA	
$I_{GES(F)}$	Gate to Emitter Forward Leakage	$V_{GE}=+30V, V_{CE}=0V$	--	--	200	nA	
$I_{GES(R)}$	Gate to Source Reverse Leakage	$V_{GE}=-30V, V_{CE}=0V$	--	--	200	nA	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=30A$	--	$T_J=25^\circ\text{C}$	1.7	1.9	V
		$V_{GE}=15V$		$T_J=150^\circ\text{C}$	1.9	--	V
$V_{GE(th)}$	Gate Threshold Voltage	$I_C=1mA, V_{CE}=V_{GE}$	4.0	5.0	6.0	V	
<b>Dynamic Characteristics</b>							
$C_{ies}$	Input Capacitance	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz$	--	3552	--	pF	
$C_{oes}$	Output Capacitance		--	106	--		
$C_{res}$	Reverse Transfer Capacitance		--	67	--		
$Q_g$	Total Gate Charge	$V_{CC}=480V, I_C=30A$ $V_{GE}=15V$	--	132	--	nC	
$Q_{ge}$	Gate to Emitter Charge		--	28	--	nC	
$Q_{gc}$	Gate to Collector Charge		--	54	--	nC	
$I_{C(SC)}$	Short circuit collector current Max.1000 short circuits Time between short circuits: $\geq 1.0s$	$V_{GE}=15V, V_{CC} \leq 400V,$ $t_{sc} \leq 3\mu s, T_J \leq 150^\circ\text{C}$	--	190	--	A	
<b>Switching Characteristics</b>							
$t_{d(ON)}$	Turn-on Delay Time	$V_{CE}=400V, I_C=30A$ $V_{GE}=0/15V, R_g=5\Omega$ Inductive Load	--	19	--	ns	
$t_r$	Rise Time		--	17	--		
$t_{d(OFF)}$	Turn-Off Delay Time		--	166	--		
$t_f$	Fall Time		--	16	--		
$E_{on}$	Turn-On Switching Loss		--	0.36	--	mJ	
$E_{off}$	Turn-Off Switching Loss		--	0.32	--		
$E_{ts}$	Total Switching Loss		--	0.68	--		

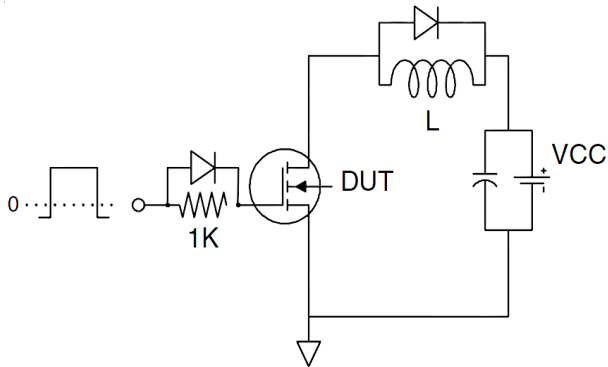
**Electrical Characteristics of the Diode ( $T_c=25^\circ\text{C}$  unless otherwise specified):**

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$V_{FM}$	Diode Forward Voltage	$I_F=15A$	--	1.5	1.7	V
$T_{rr}$	Reverse Recovery Time	$V_{CC}=400V, I_F=15A,$ $di/dt=200A/\mu s$	--	178	--	ns
$I_{RRM}$	Diode Peak Reverse Recovery Current		--	4	--	A
$Q_{rr}$	Reverse Recovery Charge		--	0.4	--	uC

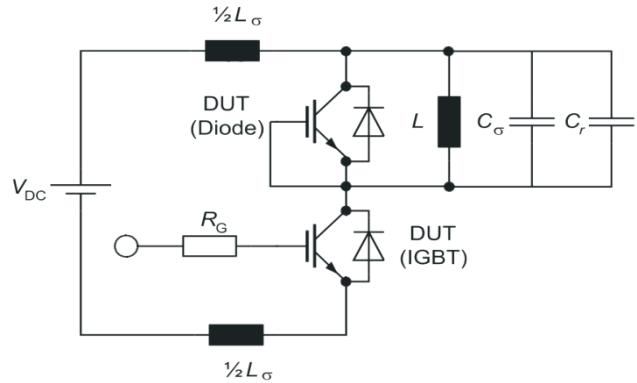
Pulse width  $t_p \leq 380\mu s, \delta \leq 2\%$

### Test Circuit

#### 1) Gate Charge Test Circuit

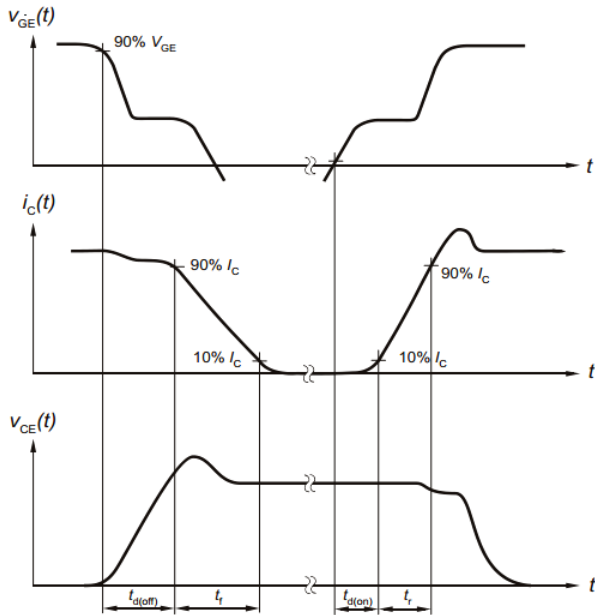


#### 2) Switch Time Test Circuit

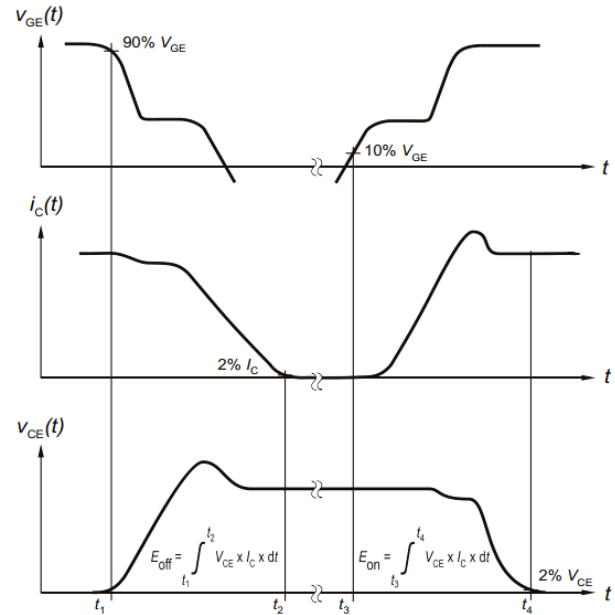


### Switching characteristics

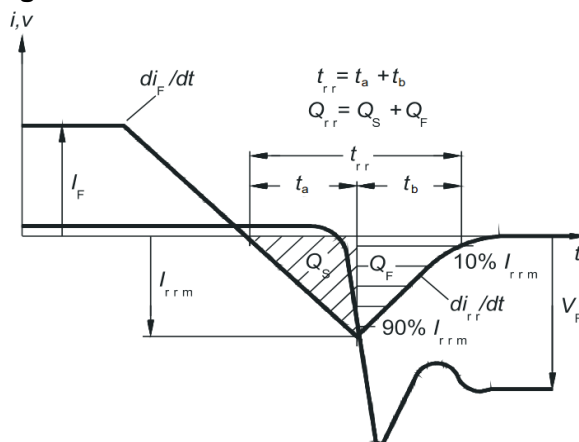
#### 1) definition of switching times



#### 2) definition of switching losses



#### 3) Definition of diode switching characteristics



Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

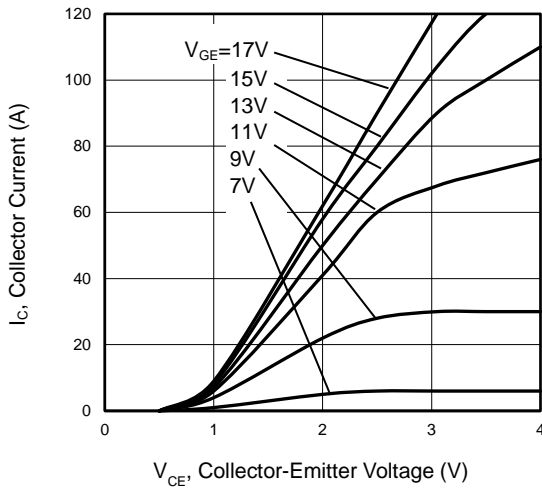


Figure 2 Transfer Characteristics

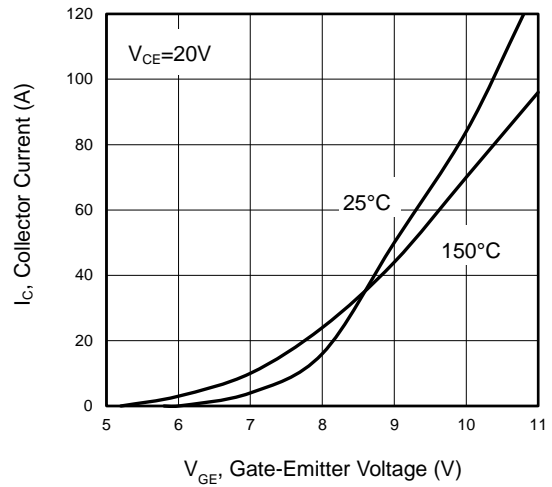


Figure 3  $V_{CEsat}$  vs. Case Temperature

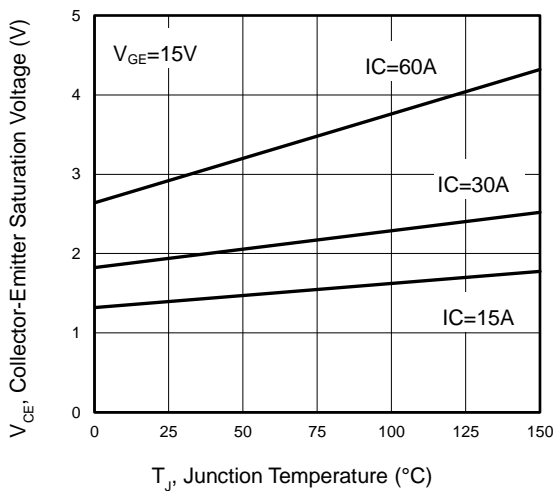


Figure 4 Saturation Voltage vs.  $V_{GE}$

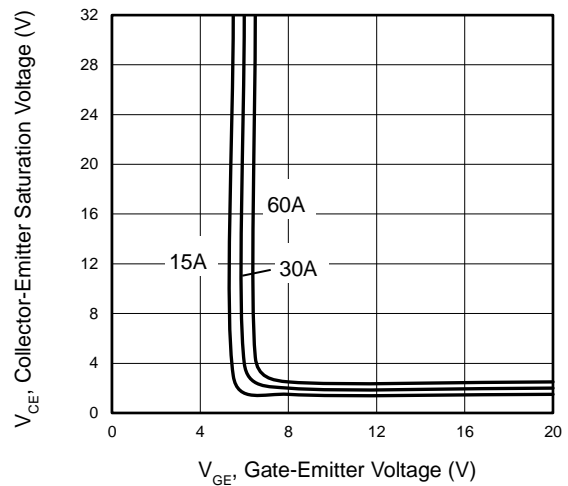


Figure 5 Capacitance Characteristics

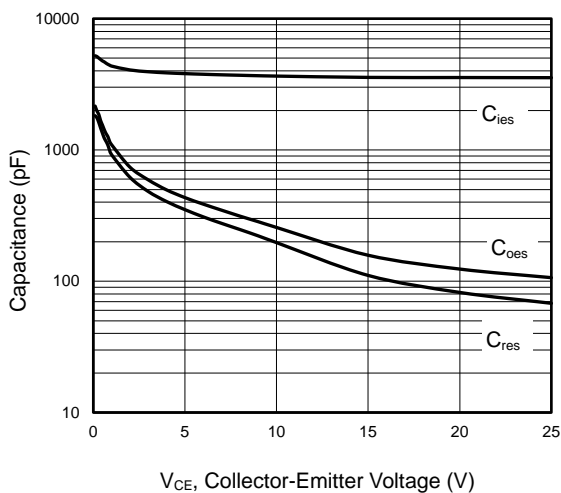
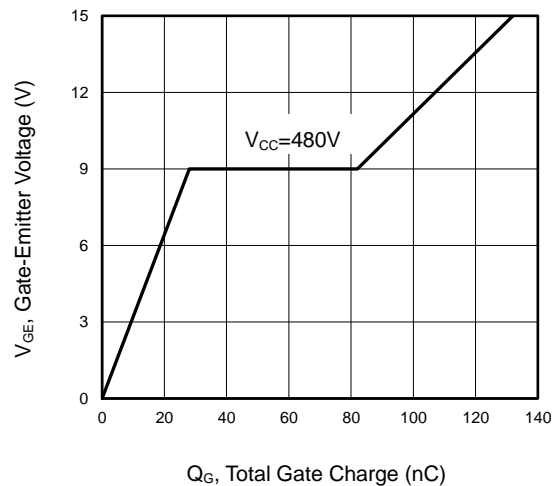


Figure 6 Gate charge waveform



Typical Electrical and Thermal Characteristics

Figure 7 Gate-emitter Threshold Voltage as a Function of Junction Temperature

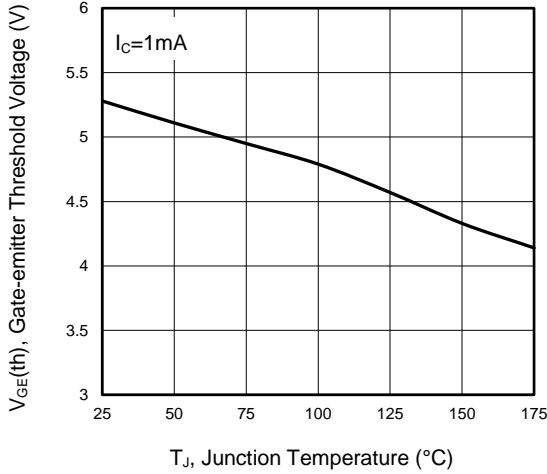


Figure 8 Power Dissipation as a Function of Case Temperature

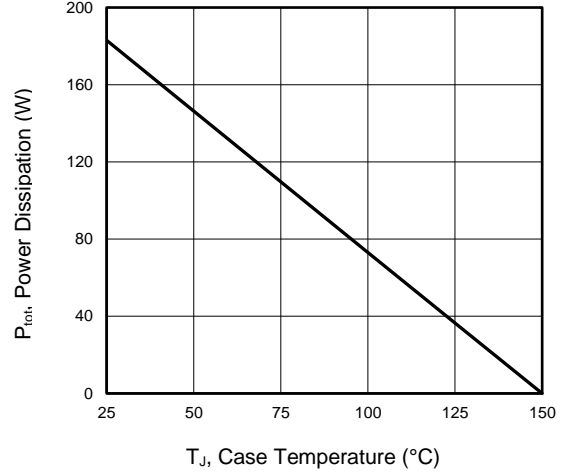


Figure 9 Typical Switching Times as a Function of Gate Resistor

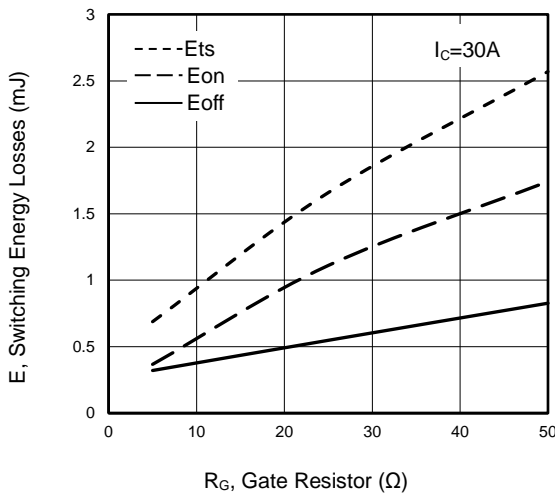


Figure 10 Typical Switching Times as a Function of Junction Temperature

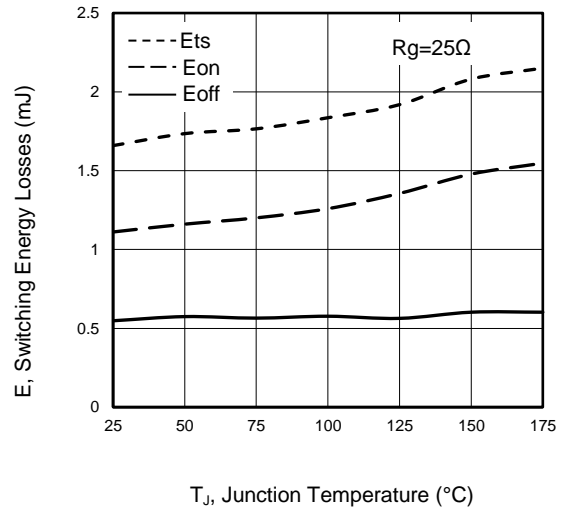


Figure 11 Typical Collector-emitter Saturation Voltage as a function of Collector Current

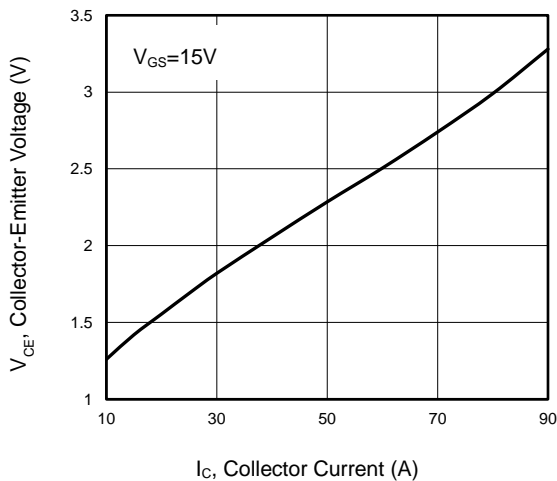
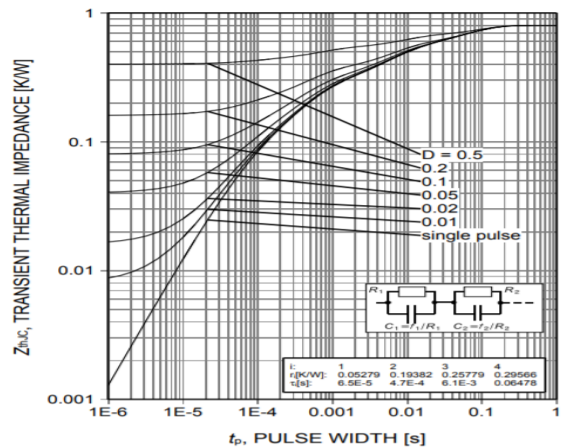
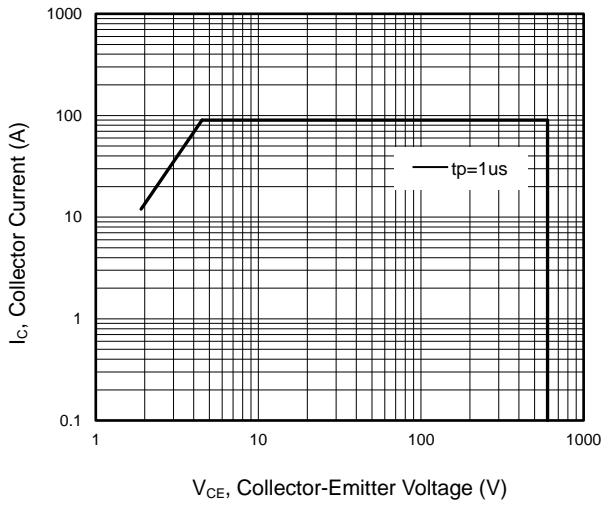


Figure 12 Transient Thermal Impedance

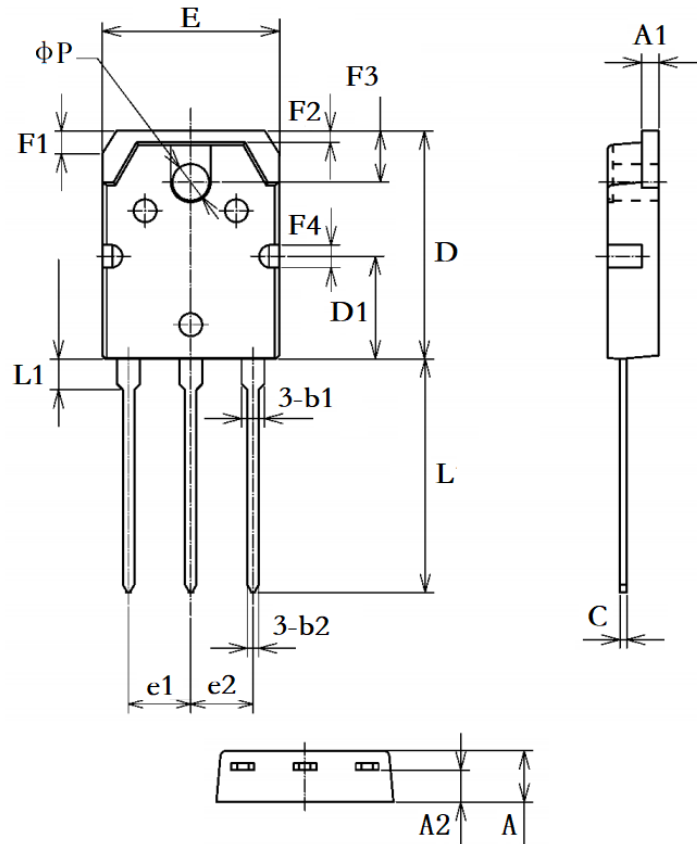


## Typical Electrical and Thermal Characteristics

Figure 13 Forward Bias Safe Operating Area



## TO-3PNT Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.35	4.65	0.17	0.18
A1	1.40	1.60	0.06	0.06
A2	2.60	3.00	0.10	0.12
b1	1.90	2.30	0.07	0.09
b2	0.90	1.10	0.04	0.04
C	0.50	0.70	0.02	0.03
D	19.70	20.30	0.78	0.80
D1	7.30	7.90	0.29	0.31
E	15.20	15.80	0.60	0.62
e1/e2	5.35	5.55	0.21	0.22
F1	1.50	2.50	0.06	0.10
F2	0.70	1.30	0.03	0.05
F3	4.60	4.90	0.18	0.19
F4	2.10	2.50	0.08	0.10
L	19.50	21.5	0.77	0.85
L1	2.10	3.30	0.08	0.13
ΦP	3.00	3.40	0.12	0.13

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